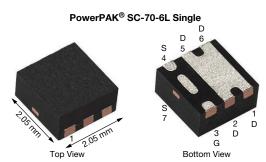
Vishay Siliconix

# N-Channel 60 V (D-S) MOSFET



| PRODUCT SUMMARY  |                    |  |  |  |  |  |  |  |
|--|--------------------|--|--|--|--|--|--|--|
| V <sub>DS</sub> (V)  | 60                 |  |  |  |  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$  | 0.0185             |  |  |  |  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$ | 0.0225             |  |  |  |  |  |  |  |
| Q <sub>g</sub> typ. (nC)                                   | 6.9                |  |  |  |  |  |  |  |
| I <sub>D</sub> (A)   | 12 <sup>a, g</sup> |  |  |  |  |  |  |  |
| Configuration  | Single             |  |  |  |  |  |  |  |

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- Very low R<sub>DS</sub> Q<sub>g</sub> Figure-of-Merit (FOM)
- Tuned for the lowest R<sub>DS</sub> Q<sub>oss</sub>
- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

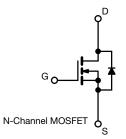


RoHS COMPLIANT

HALOGEN FREE

#### **APPLICATIONS**

- Primary side switch
- Synchronous rectification
- DC/DC converters
- · Motor drive switch
- Boost converter
- · LED backlighting



| ORDERING INFORMATION            |                 |  |  |  |  |
|---------------------------------|-----------------|--|--|--|--|
| Package                         | PowerPAK SC-70  |  |  |  |  |
| Lead (Pb)-free and halogen-free | SiA106DJ-T1-GE3 |  |  |  |  |

| ABSOLUTE MAXIMUM RATING                            | <b>S</b> (T <sub>A</sub> = 25 °C, u | ınless otherwis  | se noted)           |      |
|--|-------------------------------------|--|---------------------|------|
| PARAMETER  |                                     | SYMBOL   | LIMIT               | UNIT |
| Drain-source voltage                               |                                     | V <sub>DS</sub>  | 60                  | V    |
| Gate-source voltage                                |                                     | $V_{GS}$   | ± 20                | V    |
|  | T <sub>C</sub> = 25 °C              |  | 12 <sup>a</sup>     |      |
| Continuous dusin surrent /T 150 °C)                | T <sub>C</sub> = 70 °C              | 1 , $	extstyle 	e$ | 12 <sup>a</sup>     |      |
| Continuous drain current (T <sub>J</sub> = 150 °C) | T <sub>A</sub> =25 °C               | I <sub>D</sub>   | 10 b, c             |      |
|  | T <sub>A</sub> = 70 °C              |  | 8.1 <sup>b, c</sup> |      |
| Pulsed drain current (t = 100 μs)                  | I <sub>DM</sub>                     | 40   | Α                   |      |
|  | T <sub>C</sub> = 25 °C              |  | 12 <sup>a</sup>     |      |
| Continuous source-drain diode current              | T <sub>A</sub> = 70 °C              | I <sub>S</sub>   | 2.9 b, c            |      |
| Single pulse avalanche current                     | 1 0111                              | I <sub>AS</sub>  | 12                  |      |
| Single pulse avalanche energy                      | L = 0.1 mH                          | E <sub>AS</sub>  | 7.2                 | mJ   |
|  | T <sub>C</sub> = 25 °C              |  | 19                  |      |
| Maximum power dissipation                          | T <sub>C</sub> = 70 °C              |  | 12                  | 14/  |
|  | T <sub>A</sub> = 25 °C              | P <sub>D</sub>   | 3.5 <sup>b, c</sup> | W    |
|  | T <sub>A</sub> = 70 °C              |  | 2.2 b, c            |      |
| Operating junction and storage temperature         | T <sub>J</sub> , T <sub>stg</sub>   | -55 to +150  | °C                  |      |
| Soldering recommendations (peak tempera            |                                     | 260  |                     |      |

| THERMAL RESISTANCE RATINGS       |              |                   |         |         |      |  |  |  |  |
|----------------------------------|--------------|-------------------|---------|---------|------|--|--|--|--|
| PARAMETER                        |              | SYMBOL            | TYPICAL | MAXIMUM | UNIT |  |  |  |  |
| Maximum junction-to-ambient b, f | t ≤ 5 s      | R <sub>thJA</sub> | 28      | 36      | °C/W |  |  |  |  |
| Maximum junction-to-case (drain) | Steady state | R <sub>thJC</sub> | 5.3     | 6.5     | C/VV |  |  |  |  |

## Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<a href="www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W
- g.  $T_C = 25 \, ^{\circ}C$



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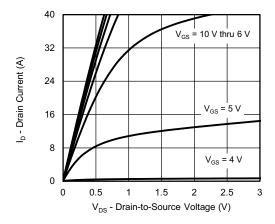
| PARAMETER                                     | SYMBOL                  | TEST CONDITIONS   | MIN. | TYP.   | MAX.   | UNIT |
|---|-------------------------|---|------|--------|--------|------|
| Static  |                         |   |      |        | l .    |      |
| Drain-source breakdown voltage                | $V_{DS}$                | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$   | 60   | -      | -      | V    |
| V <sub>DS</sub> temperature coefficient       | $\Delta V_{DS}/T_{J}$   | L 050 A   | -    | 35     | -      |      |
| V <sub>GS(th)</sub> temperature coefficient   | $\Delta V_{GS(th)}/T_J$ | $I_D = 250 \mu\text{A}$   | -    | -7.1   | -      | mV/° |
| Gate-source threshold voltage                 | V <sub>GS(th)</sub>     | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$  | 2    | -      | 4      | V    |
| Gate-source leakage                           | I <sub>GSS</sub>        | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$   | -    | -      | 100    | nA   |
| 7   |                         | $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$   | -    | -      | 1      | _    |
| Zero gate voltage drain current               | I <sub>DSS</sub>        | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C                     | -    | =      | 10     | μA   |
| On-state drain current <sup>a</sup>           | I <sub>D(on)</sub>      | $V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$  | 10   | -      | -      | Α    |
| <b>.</b>                                      | _                       | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A  | -    | 0.0142 | 0.0185 |      |
| Drain-source on-state resistance <sup>a</sup> | R <sub>DS(on)</sub>     | $V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$   | -    | 0.0166 | 0.0225 | Ω    |
| Forward transconductance a                    | 9 <sub>fs</sub>         | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A   | -    | 25     | -      | S    |
| Dynamic <sup>b</sup>                          |                         |   |      |        | L      |      |
| Input capacitance                             | C <sub>iss</sub>        |   | -    | 540    | -      | pF   |
| Output capacitance                            | C <sub>oss</sub>        | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$                          | -    | 150    | -      |      |
| Reverse transfer capacitance                  | C <sub>rss</sub>        |   | -    | 11     | -      |      |
|   |                         | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A                      | -    | 8.9    | 13.5   | nC   |
| Total gate charge                             | $Q_g$                   |   | -    | 6.9    | 10.5   |      |
| Gate-source charge                            | Q <sub>qs</sub>         | $V_{DS} = 30 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$                        | -    | 2.5    | -      |      |
| Gate-drain charge                             | Q <sub>qd</sub>         |   | -    | 1.8    | -      |      |
| Output charge                                 | Q <sub>oss</sub>        | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$   | -    | 9      | -      |      |
| Gate resistance                               | Ra                      | f = 1 MHz   | 0.3  | 1.3    | 2.6    | Ω    |
| Turn-on delay time                            | t <sub>d(on)</sub>      |   | -    | 10     | 20     |      |
| Rise time                                     | t <sub>r</sub>          | $V_{DD} = 30 \text{ V}, \text{ R}_L = 7.5 \Omega, \text{ I}_D \cong 4 \text{ A},$         | -    | 5      | 10     | ns   |
| Turn-off delay time                           | t <sub>d(off)</sub>     | $V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$  | -    | 14     | 30     |      |
| Fall time                                     | t <sub>f</sub>          |   | -    | 5      | 10     |      |
| Turn-on delay time                            | t <sub>d(on)</sub>      |   | -    | 10     | 20     |      |
| Rise time                                     | t <sub>r</sub>          | $V_{DD} = 30 \text{ V}, R_1 = 7.5 \Omega, I_D \cong 4 \text{ A},$                         | -    | 5      | 10     |      |
| Turn-off delay time                           | t <sub>d(off)</sub>     | $V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$   | -    | 12     | 25     |      |
| Fall time                                     | t <sub>f</sub>          |   | -    | 5      | 10     |      |
| <b>Drain-Source Body Diode Characteristi</b>  | cs                      |   | 1    |        |        |      |
| Continuous source-drain diode current         | I <sub>S</sub>          | T <sub>C</sub> = 25 °C  | -    | -      | 12     |      |
| Pulse diode forward current                   | I <sub>SM</sub>         |   | -    | -      | 40     | A    |
| Body diode voltage                            | V <sub>SD</sub>         | I <sub>S</sub> = 4 A, V <sub>GS</sub> = 0 V   | -    | 0.85   | 1.2    | V    |
| Body diode reverse recovery time              | t <sub>rr</sub>         |   | -    | 38     | 75     | ns   |
| Body diode reverse recovery charge            | Q <sub>rr</sub>         |   | -    | 23     | 45     | nC   |
| Reverse recovery fall time                    | ta                      | $I_F = 4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$ | -    | 17     | -      |      |
| Reverse recovery rise time                    | t <sub>b</sub>          |   | -    | 21     | -      | ns   |

#### **Notes**

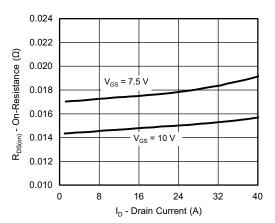
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

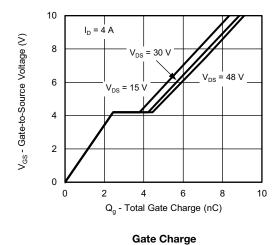


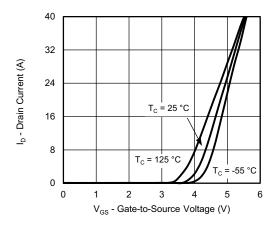


#### **Output Characteristics**

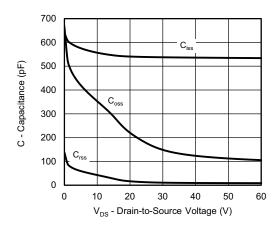


On-Resistance vs. Drain Current and Gate Voltage

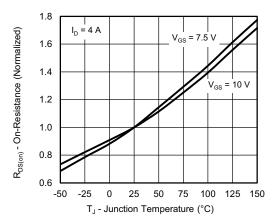




**Transfer Characteristics** 

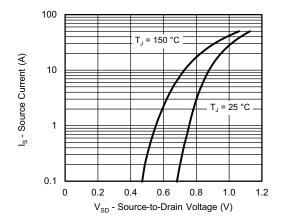


Capacitance

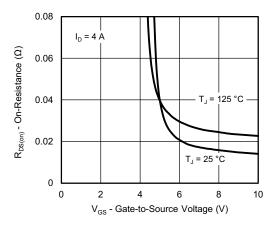


On-Resistance vs. Junction Temperature

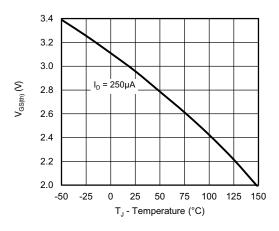




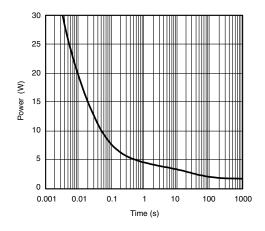
Source-Drain Diode Forward Voltage



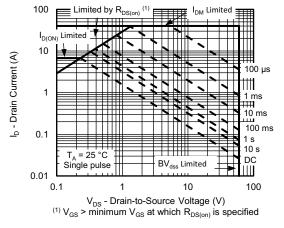
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

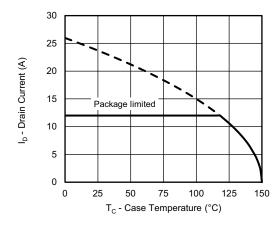


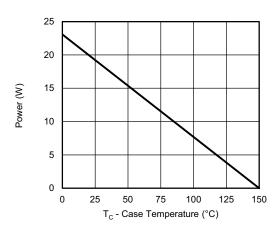
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient







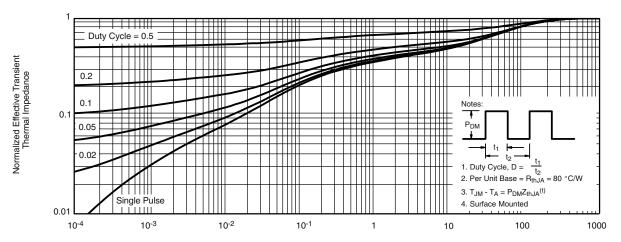
Current Derating a

Power, Junction-to-Case

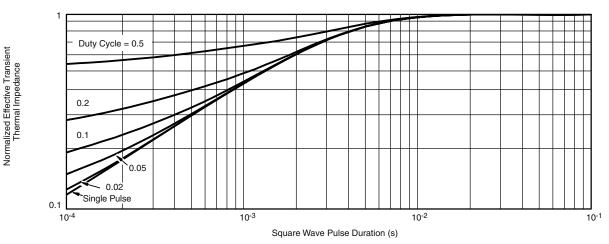
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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Vishay Siliconix

# PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

|     | SINGLE PAD  |           |       |           |           |           | DUAL PAD    |       |           |           |       |       |
|-----|-------------|-----------|-------|-----------|-----------|-----------|-------------|-------|-----------|-----------|-------|-------|
| DIM | MILLIMETERS |           |       | INCHES    |           |           | MILLIMETERS |       |           | INCHES    |       |       |
|     | Min         | Nom       | Max   | Min       | Nom       | Max       | Min         | Nom   | Max       | Min       | Nom   | Max   |
| Α   | 0.675       | 0.75      | 0.80  | 0.027     | 0.030     | 0.032     | 0.675       | 0.75  | 0.80      | 0.027     | 0.030 | 0.032 |
| A1  | 0           | -         | 0.05  | 0         | -         | 0.002     | 0           | -     | 0.05      | 0         | -     | 0.002 |
| b   | 0.23        | 0.30      | 0.38  | 0.009     | 0.012     | 0.015     | 0.23        | 0.30  | 0.38      | 0.009     | 0.012 | 0.015 |
| С   | 0.15        | 0.20      | 0.25  | 0.006     | 0.008     | 0.010     | 0.15        | 0.20  | 0.25      | 0.006     | 0.008 | 0.010 |
| D   | 1.98        | 2.05      | 2.15  | 0.078     | 0.081     | 0.085     | 1.98        | 2.05  | 2.15      | 0.078     | 0.081 | 0.085 |
| D1  | 0.85        | 0.95      | 1.05  | 0.033     | 0.037     | 0.041     | 0.513       | 0.613 | 0.713     | 0.020     | 0.024 | 0.028 |
| D2  | 0.135       | 0.235     | 0.335 | 0.005     | 0.009     | 0.013     |             |       |           |           |       |       |
| Е   | 1.98        | 2.05      | 2.15  | 0.078     | 0.081     | 0.085     | 1.98        | 2.05  | 2.15      | 0.078     | 0.081 | 0.085 |
| E1  | 1.40        | 1.50      | 1.60  | 0.055     | 0.059     | 0.063     | 0.85        | 0.95  | 1.05      | 0.033     | 0.037 | 0.041 |
| E2  | 0.345       | 0.395     | 0.445 | 0.014     | 0.016     | 0.018     |             |       |           |           |       |       |
| E3  | 0.425       | 0.475     | 0.525 | 0.017     | 0.019     | 0.021     |             |       |           |           |       |       |
| е   |             | 0.65 BSC  |       |           | 0.026 BSC | ;         | 0.65 BSC    |       |           | 0.026 BSC |       |       |
| K   |             | 0.275 TYP |       |           | 0.011 TYP |           | 0.275 TYP   |       |           | 0.011 TYP |       |       |
| K1  |             | 0.400 TYP |       | 0.016 TYP |           |           | 0.320 TYP   |       |           | 0.013 TYP |       |       |
| K2  |             | 0.240 TYP |       | 0.009 TYP |           | 0.252 TYP |             |       | 0.010 TYP |           |       |       |
| К3  |             | 0.225 TYP |       | 0.009 TYP |           |           |             |       |           | •         | •     |       |
| K4  |             | 0.355 TYP |       | 0.014 TYP |           |           |             |       |           |           |       |       |
| L   | 0.175       | 0.275     | 0.375 | 0.007     | 0.011     | 0.015     | 0.175       | 0.275 | 0.375     | 0.007     | 0.011 | 0.015 |
| T   |             |           |       |           |           |           | 0.05        | 0.10  | 0.15      | 0.002     | 0.004 | 0.006 |

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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